54ABT573

FEATURES

- 54ABT573 is the broadside pinout version of 54ABT373
- Inputs and outputs on opposite side of package allow easy interface to Microprocessors
- 3-State outputs for bus interfacing common output enable
- Latch-up protection exceeds 500mA per JEDEC JC40.2 Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model

DESCRIPTION

The 54ABT573 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 54ABT573 device is an octal transparent latch coupled to eight 3-State output buffers. The two sections of the device are controlled independently by Enable (E) and Output Enable (OE) control gates. The 54ABT573 is functionally identical to the 54ABT373 but has a broadside pinout configuration to facilitate PC board layout and allow easy interface with microprocessors.

The data on the D inputs are transferred to the latch outputs when the Latch Enable (E)

input is High. The latch remains transparent to the data inputs while E is High, and stores the data that is present one setup time before the High-to-Low enable transition.

The 3-State output buffers are designed to drive heavily loaded 3-State buses, MOS memories, or MOS microprocessors. The active-Low Output Enable (ŌE) controls all eight 3-State buffers independent of the latch operation.

When OE is Low, the latched or transparent data appears at the outputs. When OE is High, the outputs are in the High-impedance "OFF" state, which means they will neither drive nor load the bus.

ORDERING INFORMATION

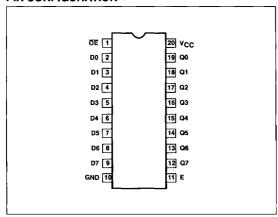
DESCRIPTION	ORDER CODE	PACKAGE DESIGNATOR*
20-Pin Ceramic DIP	54ABT573/BRA	GDIP1-T20
20-Pin Ceramic LLCC	54ABT573/B2A	CQCC2-N20

^{*} MIL-STD 1835 or Appendix A of 1995 Military Data Handbook

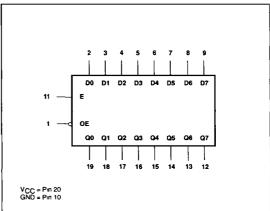
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1	ŌĒ	Output enable input (active Low)
2, 3, 4, 5 6, 7, 8, 9	D0 - D7	Data inputs
19, 18, 17, 16, 15, 14, 13, 12	Q0 - Q7	3-State outputs
11	E	Enable input (active High)
10	GND	Ground (0V)
20	Vcc	Positive supply voltage

PIN CONFIGURATION

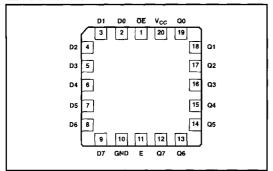


LOGIC SYMBOL



54ABT573

LLCC LEAD CONFIGURATION



FUNCTION TABLE

	INPUTS		INTERNAL	OUTPUTS	OPERATING MODE
ŌĒ	E	- Dn	REGISTER	Q0 - Q7	
L	ıπ	L H	Ή	H	Enable and read register
L	\rightarrow	h	Н	L	Latch and read register
L	Ĺ	Х	NC	NC	Hold
H	٦	X Dn	NC Dn	Z Z	Disable outputs

H ≠ High voltage level

h = High voltage level one setup time prior to the High-to-Low E transition

L = Low voltage level

Low voltage level one setup time prior to the High-to-Low E transition

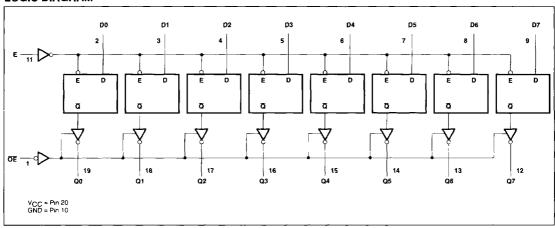
NC= No change

X = Don't care

Z = High impedance "off" state

↓ = High-to-Low E transition

LOGIC DIAGRAM



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ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage range		-0.5 to +7.0	V
lık	DC input diode current	V _I < 0	-18	mA
VI	DC input voltage range ³		-1.2 to +7.0	٧
lok	DC output diode current	V _O < 0	-50	mA
ν _o	DC output voltage range ³	Output in Off or High state	-0.5 to +5.5	٧
lo	DC output current	Output in Low state	96	mA
T _{STG}	Storage temperature range		-65 to +150	°C

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	UNIT	
	·	MIN	MAX	1
V _{CC}	DC supply voltage	4.5	5.5	٧
Ví	Input voltage	0	Vcc	ν
V _{IH}	High-level input voltage	2.0		٧
V _{IL}	Low-level input voltage		0.8	V
Іон	High-level output current		-24	mA
lor	Low-level output current		48	mA
Δt/Δν	Input transition rise or fall rate	0	5	ns/V
T _{amb}	Operating free-air temperature range	-55	+125	°C

DC ELECTRICAL CHARACTERISTICS

 V_{CC} = MAX, V_{I} = V_{IL} or V_{IH} unless otherwise noted.

SYMBOL	PARAMETER	TEST CONDITIONS			LIMITS			UNIT
				T _{amb} ≈ +25°C			T _{amb} = -55 to +125°C	
	j		MIN	TYP ²	MAX	MIN	MAX	
V _{IK}	input clamp voltage	V _{CC} ≈ 4.5V, I _{IK} = -18mA			-1.2		-1.2	٧
		V _{CC} ≈ 4.5V; I _{OH} = -3mA	2.5	3.0		2.5		٧
V _{OH}	High-level output to voltage	V _{CC} ≈ 5.0V; I _{OH} = -3mA	3.0	3.5		3.0		٧
		V _{CC} = 4.5V; I _{OH} = -24mA	2.0	2.4		2.0		٧
V _{OL}	Low-level output voltage	V _{CC} ≈ 4.5V; I _{OL} = 48mA		0.42	0.55		0.55	>
J _t	Input leakage current	$V_l = GND \text{ or } 5.5V$		±0.01	±1.0		±1.0	μА
lozh	3-State output High current	$V_0 = 2.7V, V_1 = V_{1L} \text{ or } 3.0V^8$		0.5	10		10	μА
l _{OZL}	3-State output Low current	$V_O = 0.5V$, $V_I = V_{IL}$ or $3.0V^8$		-0.5	-10		-10	μA
I _O	Short-circuit output current4	$V_O = 2.5V$, $V_I = GND$ or V_{CC}	-50	-100	-180	-50	-180	mA
1 _{ССН}		Outputs High, V _I = GND or V _{CC}		0.5	250		250	μА
I _{CCL}	Quiescent supply current	Outputs Low, V _I = GND or V _{CC}		24	30		30	mA
I _{CCZ}	7	Outputs 3-State, $V_{j} = GND$ or V_{CC}		0.5	250		250	μА
Δl _{CC}	Additional supply current per input pin ⁵	One input at 3.4V, other inputs at V _{CC} or GND		0.5	1.5		1.5	mA
loff	Power OFF leakage current	$V_{CC} = 0.0V, V_{I} \text{ or } V_{O} \le 4.5V$	-100	1.0	100			μА
I _{CEX}	Output High leakage current	$V_{CC} = 5.5V, V_{O} = 5.5V$			50		50	μΑ

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AC ELECTRICAL CHARACTERISTICS

GND = 0V, t_R = t_F = 2.5ns, C_L = 50pF, R_L = 500 Ω

SYMBOL	PARAMETER	WAVEFORM	T	LIMITS				UNIT
				T _{amb} = +25°C V _{CC} = +5.0V				
			MIN	TYP	MAX	MIN	MAX	
t _{PLH}	Propagation delay Dn to Qn	Waveform 13	1.9 2.2	3.2 4.2	5.4 5.7	1.4 1.6	6.4 6.7	ns ns
t _{PLH} t _{PHL}	Propagation delay E to Qn	Waveform 12	2.2 3.2	4.0 5.2	6.1 6.7	2.0 2.8	7.1 7.5	ns ns
t _{PZH} t _{PZL}	Output enable time to High and Low level	Waveform 15 Waveform 16	1.2 2.7	3.2 4.7	4.7 6.2	0.8 2.0	6.2 7.2	ns ns
t _{PHZ}	Output disable time from High and Low level	Waveform 15 Waveform 16	2.5 2.0	4.9 4.2	6.4 6.0	2.2 1.4	7.7 7.0	ns ns

AC SETUP REQUIREMENTS

GND = 0V, $t_R = t_F = 2.5 \text{ns}$, $C_L = 50 \text{pF}$, $R_L = 500 \Omega$

SYMBOL	PARAMETER	WAVEFORM		LIMITS				UNIT
				T _{amb} = +25°C V _{CC} = +5.0V		$T_{amb} = -55^{\circ}C \text{ to } +125^{\circ}C$ $V_{CC} = +5.0V \pm 0.5V$		
			MIN	TYP	MAX	MIN	MAX	
t _s (H) t _s (L)	Setup time ⁶ Dn to E	Waveform 14	2.0 2.0			2.5 2.5		ns ns
t _h (H) t _h (L)	Hold time6 Dn to E	Waveform 14	2.0 2.0			2.5 2.5		ns ns
t _w (H)	E pulse width ⁷ High or Low	Waveform 12	3.3			3.3		ns

NOTES:

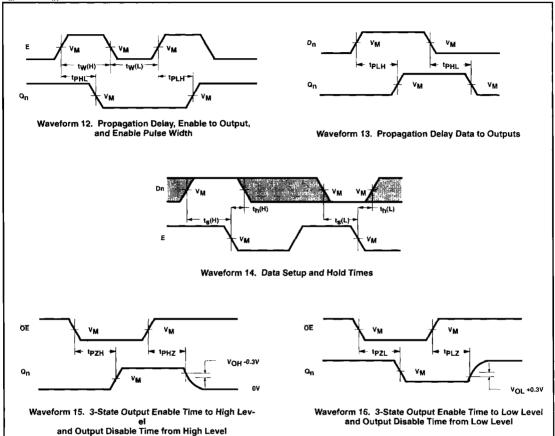
- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the
 device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to
 absolute-maximum-rated conditions for extended periods may affect device reliability.
- The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
- 3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 4. Not more than one output should be tested at a time, and the4 duration of the test should not exceed one second.
- 5. This is the increase in supply current for each input at 3.4V.
- 6. t_{set} and t_{hold} limits that are less than 3.0ns are guaranteed, but are only tested to a 3.0ns limit due to tester limitations.
- 7. tw limits that are less than 6.0ns are guaranteed, but are only tested to a 6.0ns limit due to tester limitations.
- 8. To accommodate tester limitations, I_{OZ} tests are tested with V_{IH} = 3.0V, but 2.0V V_{IH} is guaranteed.

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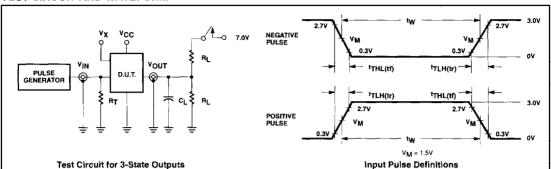
AC WAVEFORMS





54ABT573

TEST CIRCUIT AND WAVEFORM



Test Circuit for 3-State Outputs

SWITCH POSITION

TEST	SWITCH
[†] PLZ.	closed
[†] PZL	closed
All other	open

INPUT PULSE REQUIREMENTS							
Family Amplitude Rep. Rate t _W t _R t _F							
54ABT	3.0V	1MHz	500ns	2.5ns	2.5ns		

DEFINITIONS:

R_L = Load Resistor; see AC Characteristics for value.

 $R_{\rm L} = {\rm Load}$ capacitance includes jig and probe capacitance; see AC Characteristics for value. $R_{\rm T} = {\rm Termination}$ resistance should be equal to $Z_{\rm OUT}$ of pulse generators.